

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

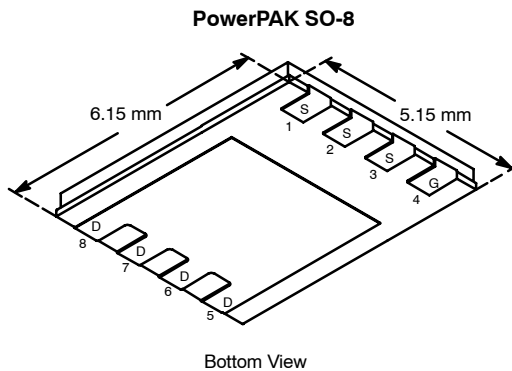
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.003 @ $V_{GS} = 10$ V	30
	0.004 @ $V_{GS} = 4.5$ V	27

FEATURES

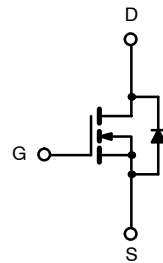
- Ultra-Low On-Resistance Using High Density TrenchFET® Gen II Power MOSFET Technology
- New Low Thermal Resistance PowerPAK® Package with Low 1.07-mm Profile

APPLICATIONS

- Low-Side DC/DC Conversion
 - Notebook
 - Server
 - Workstation
- Point-of-Load Conversion



Ordering Information: Si7356DP-T1



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	30	18	A
	T _A = 70°C		25	15	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	70		
Continuous Source Current (Diode Conduction) ^a		I _S	4.5	1.8	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	5.4	1.9	W
	T _A = 70°C		3.4	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	18	23	$^\circ\text{C/W}$
	Steady State		50	65	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.5	

Notes

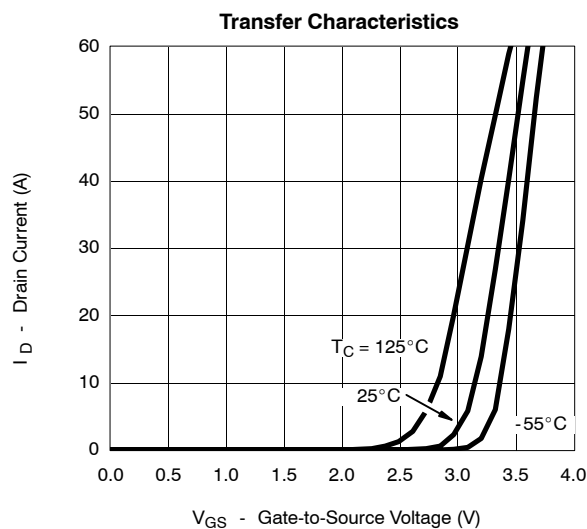
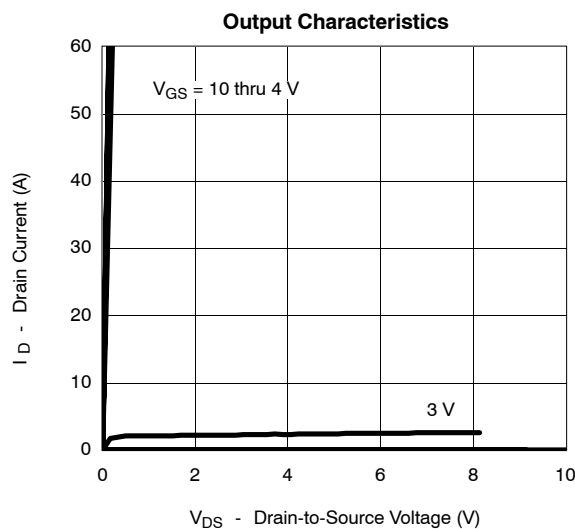
a. Surface Mounted on 1" x 1" FR4 Board.

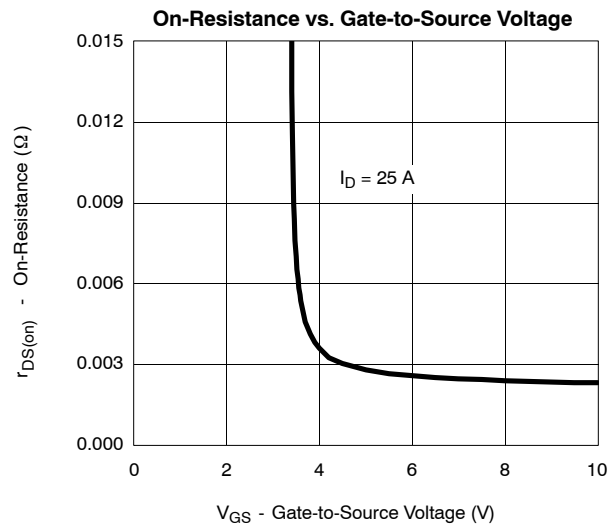
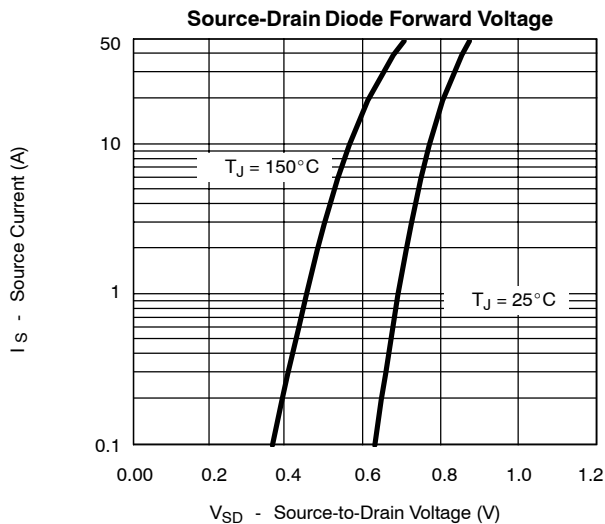
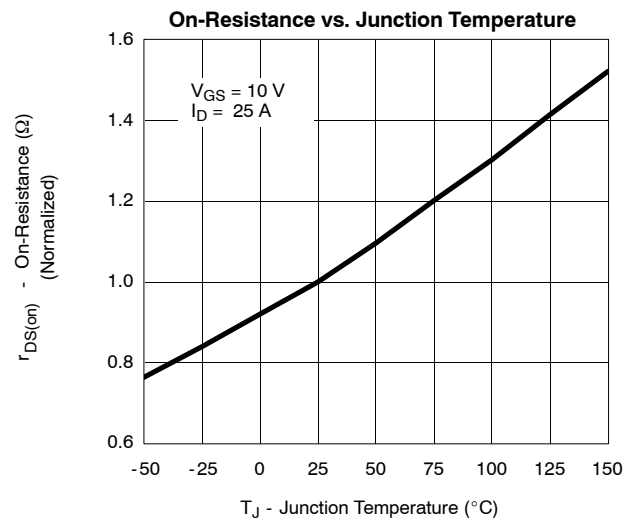
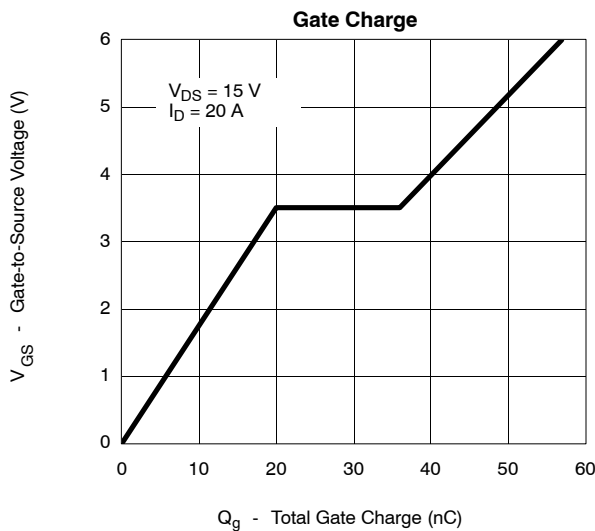
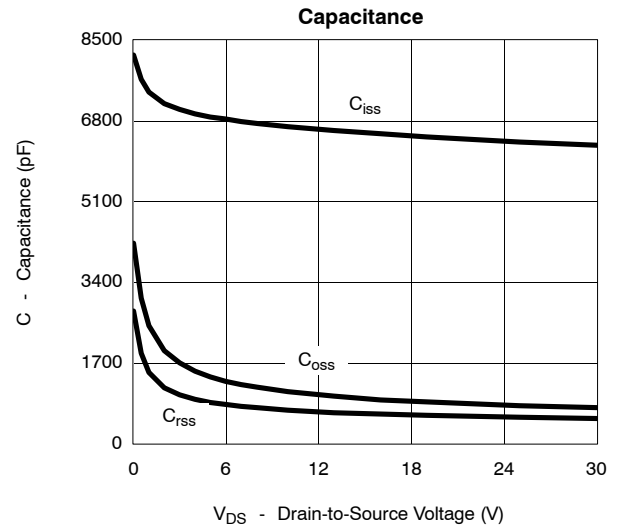
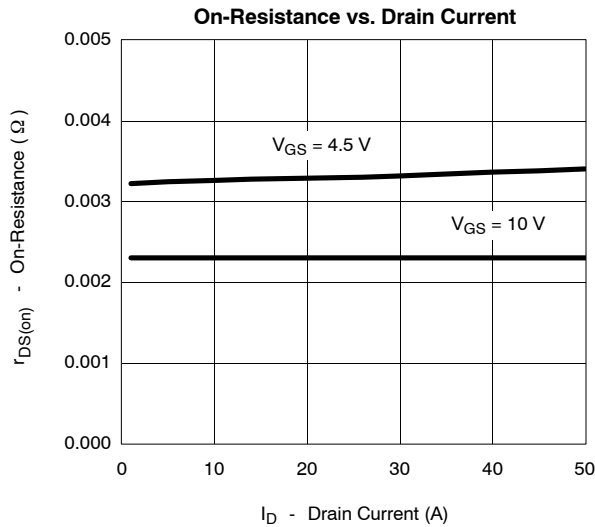
MOSFET SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

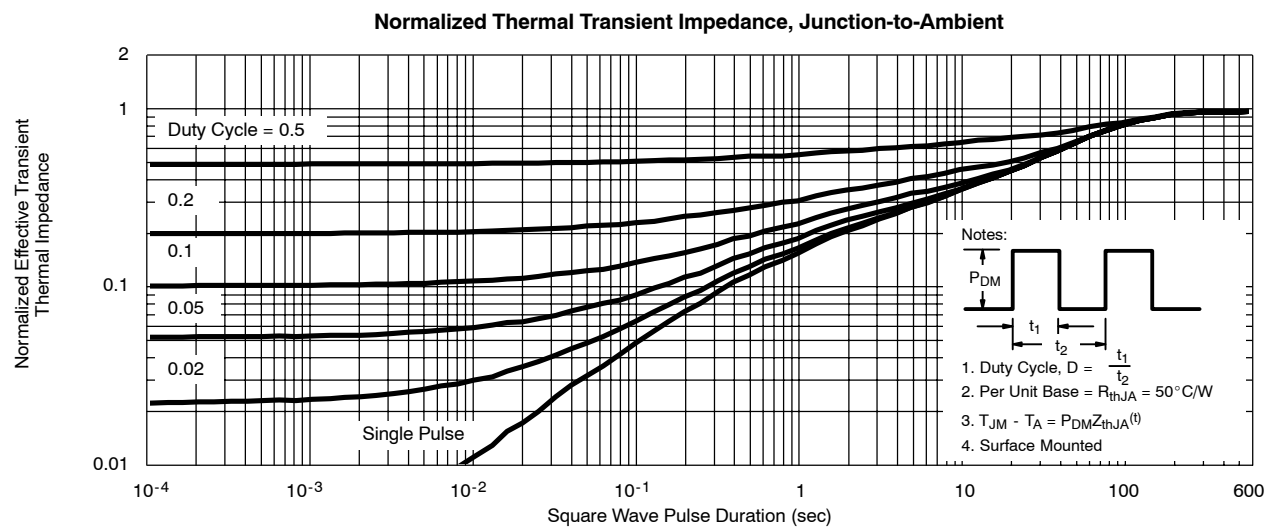
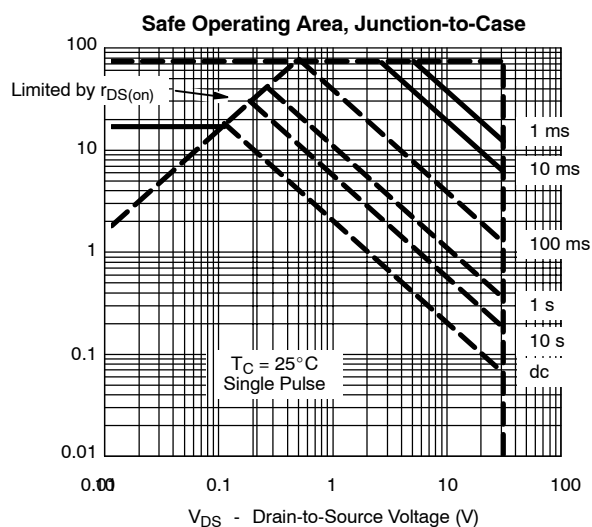
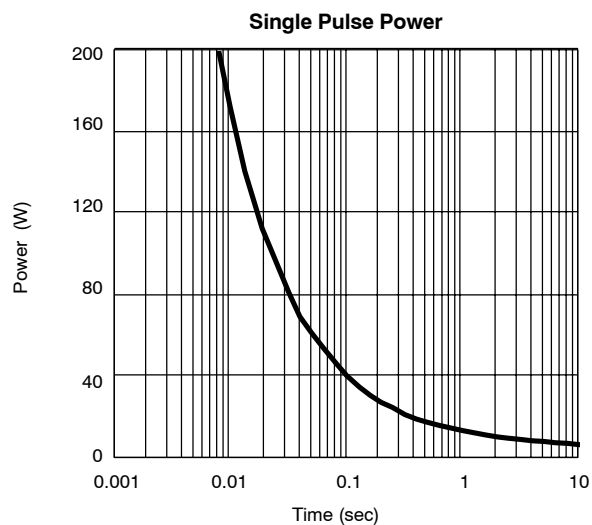
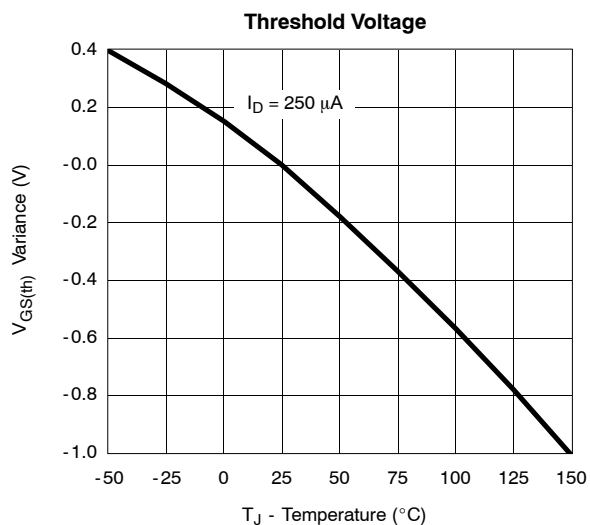
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 24\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^{NO TAG}	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance ^{NO TAG}	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 25\ \text{A}$		0.0024	0.003	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 19\ \text{A}$		0.0032	0.004	
Forward Transconductance ^{NO TAG}	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 25\ \text{A}$		110		S
Diode Forward Voltage ^{NO TAG}	V_{SD}	$I_S = 2.9\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.72	1.1	V
Dynamic^{NO TAG}						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 4.5\ \text{V}$, $I_D = 20\ \text{A}$		45	70	nC
Gate-Source Charge	Q_{gs}			20		
Gate-Drain Charge	Q_{gd}			16		
Gate Resistance	R_G			1.1		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		27	40	ns
Rise Time	t_r			21	35	
Turn-Off Delay Time	$t_{d(off)}$			107	160	
Fall Time	t_f			43	65	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.9\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		45	70	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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